



# BT139-600E

## 4Q Triac

Rev. 04 — 24 February 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 1.2 Features and benefits

- High blocking voltage capability
- High noise immunity
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

### 1.3 Applications

- General purpose motor control
- General purpose switching

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		<a href="#">[1]</a> -	-	600	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; see <a href="#">Figure 4</a> ; see <a href="#">Figure 5</a>	-	-	155	A
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99\text{ °C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a> ; see <a href="#">Figure 3</a>	-	-	16	A



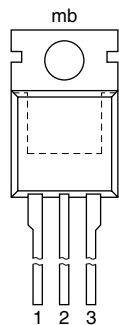
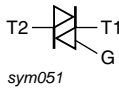
Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 7</a>	-	2.5	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 7</a>	-	4	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 7</a>	-	5	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 7</a>	-	11	25	mA

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ms.

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

SOT78 (TO-220AB)

## 3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BT139-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78
BT139-600E/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

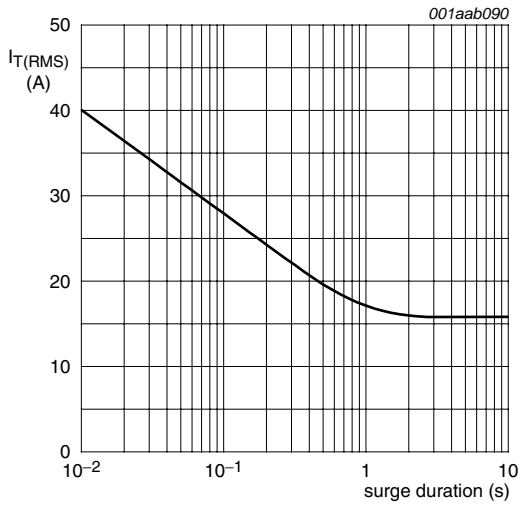
## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

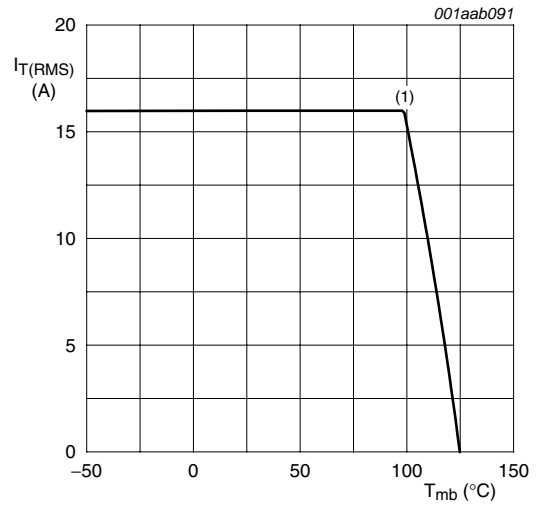
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		[1] -	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99\text{ °C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a> ; see <a href="#">Figure 3</a>	-	16	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; see <a href="#">Figure 4</a> ; see <a href="#">Figure 5</a>	-	155	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	170	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	120	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_T = 20\text{ A}$ ; $I_G = 200\text{ mA}$ ; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G+	-	50	A/ $\mu\text{s}$
		$I_T = 20\text{ A}$ ; $I_G = 200\text{ mA}$ ; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G-	-	50	A/ $\mu\text{s}$
		$I_T = 20\text{ A}$ ; $I_G = 200\text{ mA}$ ; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G-	-	50	A/ $\mu\text{s}$
		$I_T = 20\text{ A}$ ; $I_G = 200\text{ mA}$ ; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G+	-	10	A/ $\mu\text{s}$
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	125	°C

- [1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ms.



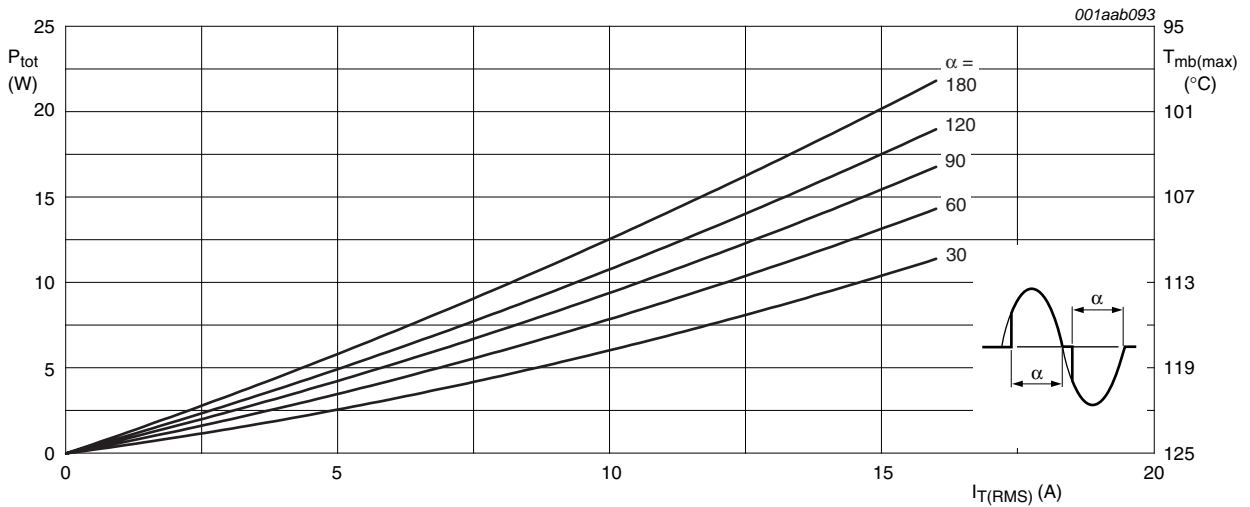
f = 50 Hz  
 $T_{mb} \leq 99\text{ }^{\circ}\text{C}$

Fig 1. RMS on-state current as a function of surge duration; maximum values



(1)  $T_{mb} = 99\text{ }^{\circ}\text{C}$

Fig 2. RMS on-state current as a function of mounting base temperature; maximum values



$\alpha$  = conduction angle

Fig 3. Total power dissipation as a function of RMS on-state current; maximum values.

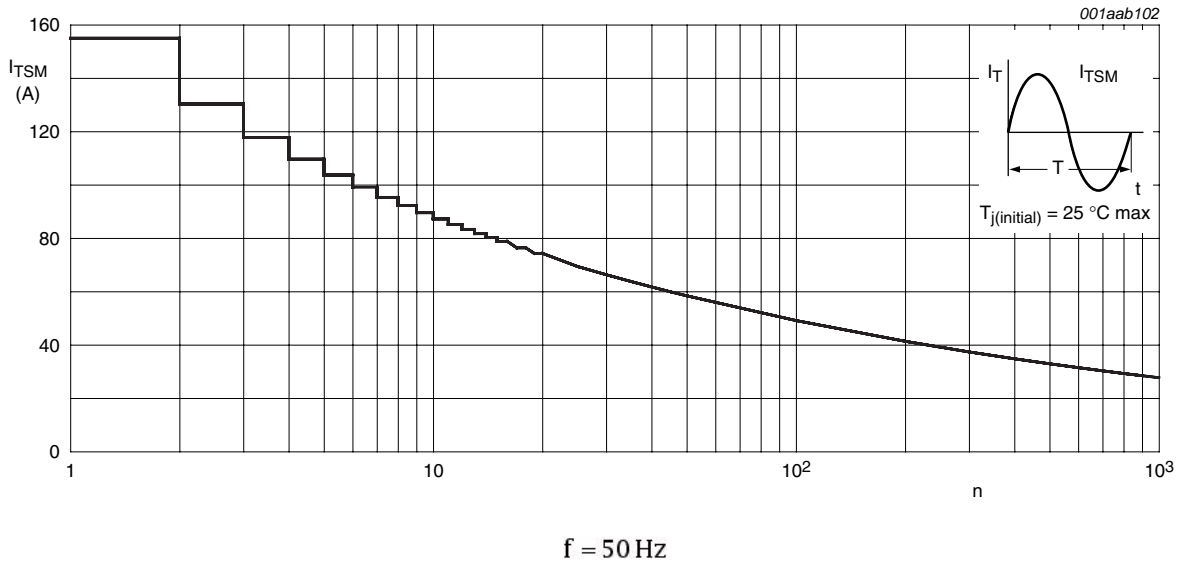


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

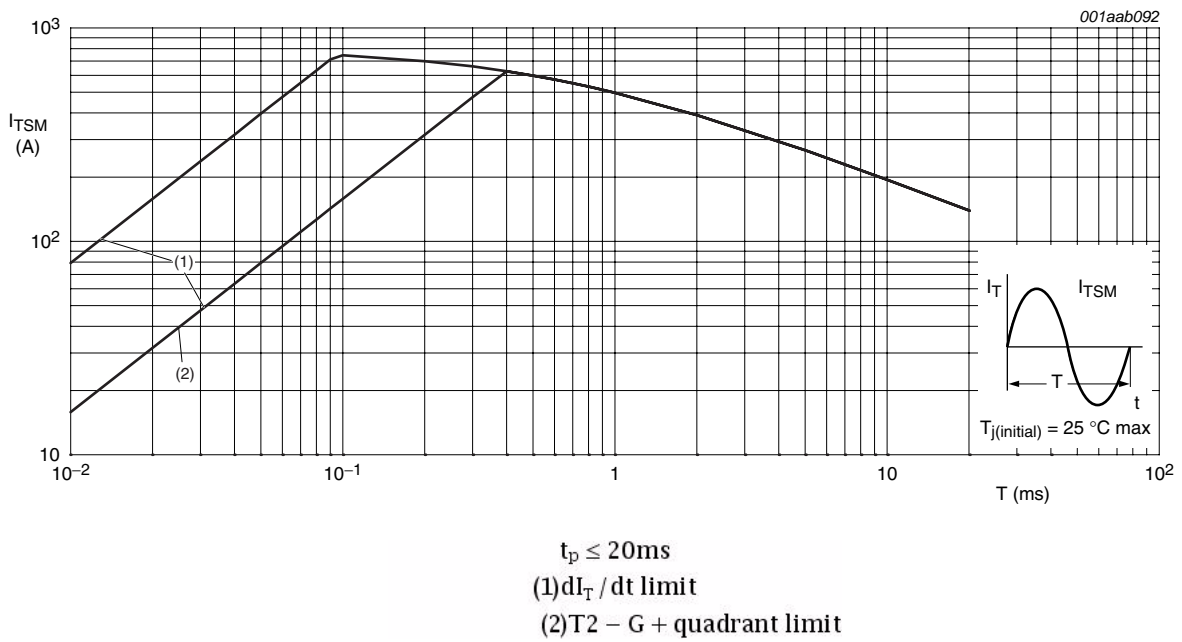
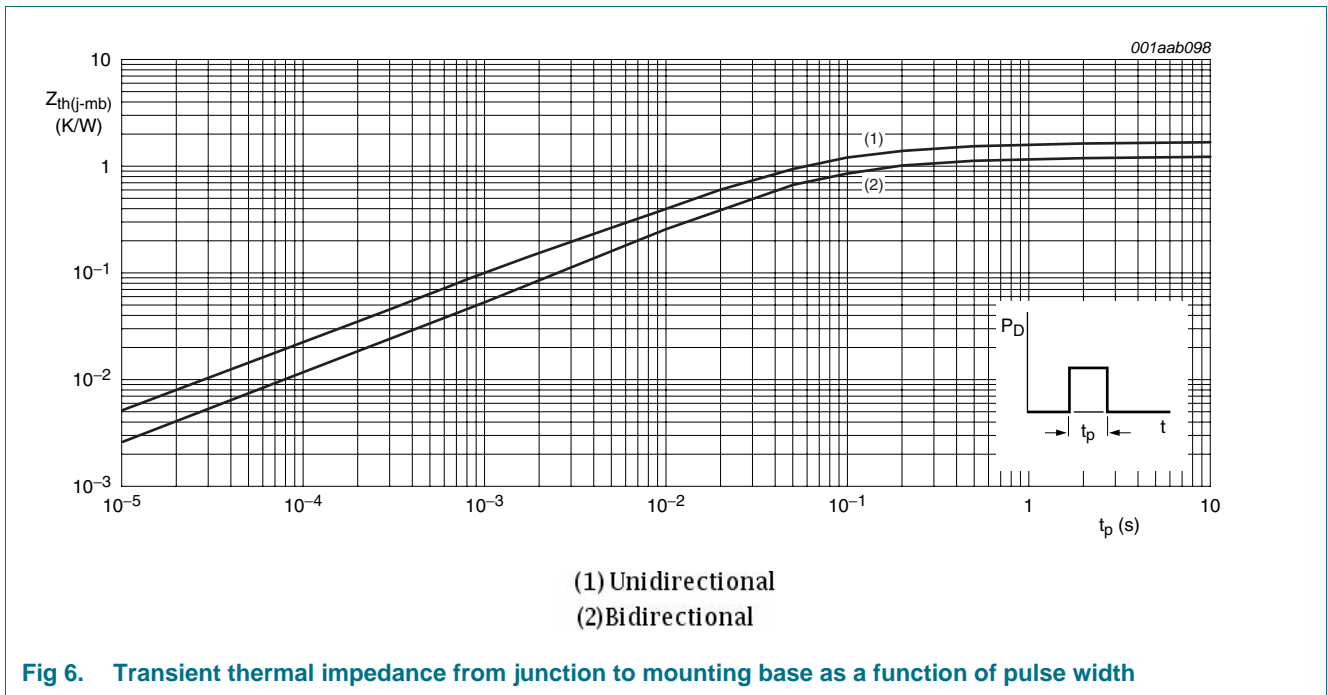


Fig 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

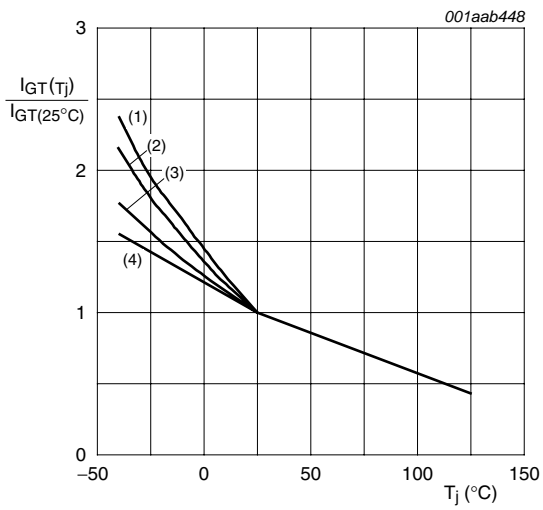
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; see <a href="#">Figure 6</a>	-	-	1.7	K/W
		full cycle; see <a href="#">Figure 6</a>	-	-	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle	-	60	-	K/W



## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 7</a>	-	2.5	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 7</a>	-	4	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 7</a>	-	5	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 7</a>	-	11	25	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	3.2	30	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	16	40	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	4	30	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	5.5	40	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 9</a>	-	4	45	mA
$V_T$	on-state voltage	$I_T = 20\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 10</a>	-	1.2	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 11</a>	-	0.7	1.5	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ °C}$	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 402\text{ V}$ ; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; exponential waveform; gate open circuit	-	50	-	V/ $\mu$ s
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$ ; $V_D = 600\text{ V}$ ; $I_G = 100\text{ mA}$ ; $dI_G/dt = 5\text{ A}/\mu$ s	-	2	-	$\mu$ s



- (1) T2 – G +
- (2) T2 + G –
- (3) T2 – G –
- (4) T2 + G +

Fig 7. Normalized gate trigger current as a function of junction temperature

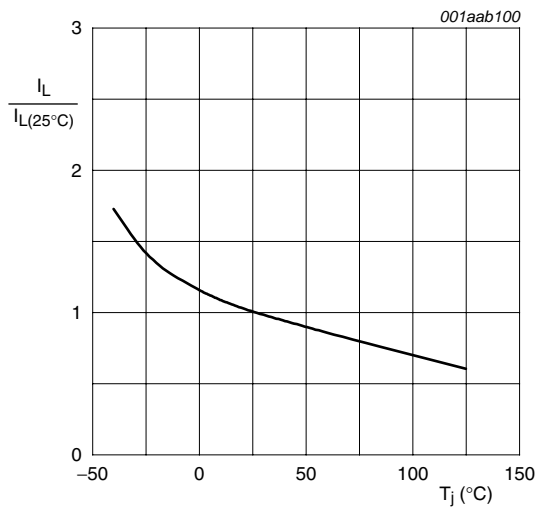


Fig 8. Normalized latching current as a function of junction temperature

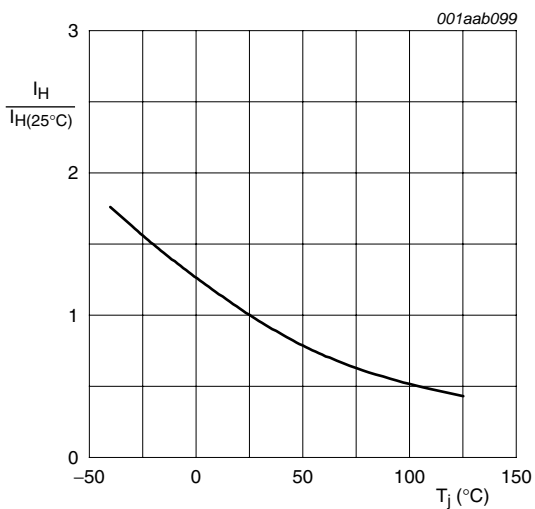
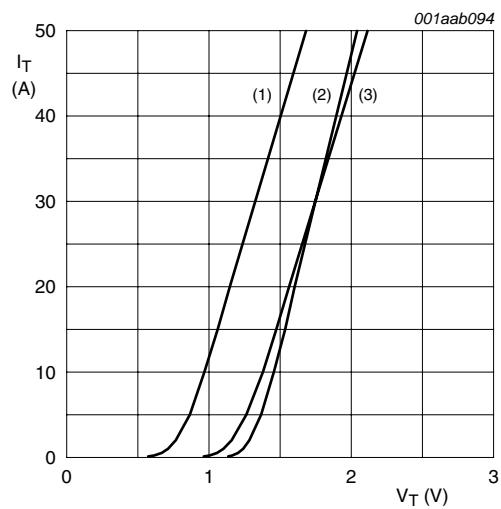


Fig 9. Normalized holding current as a function of junction temperature



- $V_o = 1.195\text{ V}$   
 $R_s = 0.018\ \Omega$
- (1)  $T_j = 125\text{ }^\circ\text{C}$ ; typical values
  - (2)  $T_j = 25\text{ }^\circ\text{C}$ ; maximum values
  - (3)  $T_j = 125\text{ }^\circ\text{C}$ ; maximum values

Fig 10. On-state current as a function of on-state voltage



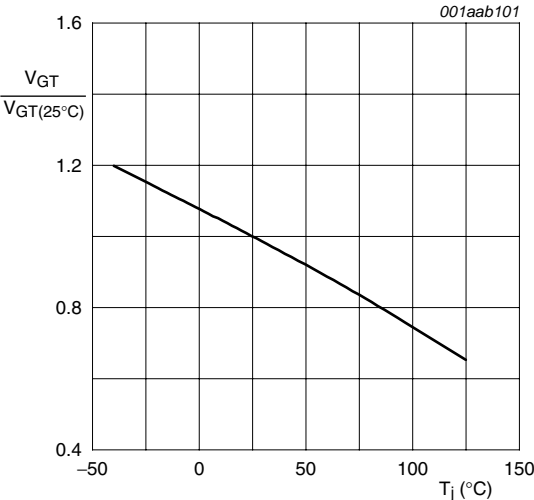


Fig 11. Normalized gate trigger voltage as a function of junction temperature

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



Fig 12. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BT139-600E v.4	20110224	Product data sheet	-	BT139_SER_E v.3
Modifications:	<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Type number BT139-600E separated from data sheet BT139_SER_E v.3.</li></ul>			
BT139_SER_E v.3	20040923	Product data sheet	-	BT139_SERIES_E v.2

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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